

## PUMB9

# 50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$

4 January 2023

**Product data sheet** 

## 1. General description

PNP/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PUMD9 NPN/NPN complement: PUMH9

#### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

## 3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replaces general-purpose transistors in digital applications

#### 4. Quick reference data

#### Table 1. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-50	V
Io	output current			-	-	-100	mA
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			3.7	4.7	5.7	



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## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	l1	input (base) TR1		
3	O2	output (collector) TR2	<u> </u>	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3	
			TSSOP6 (SOT363)	GND1 I1 O2
				006aaa212

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PUMB9		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PUMB9	B%9

[1] % = placeholder for manufacturing site code

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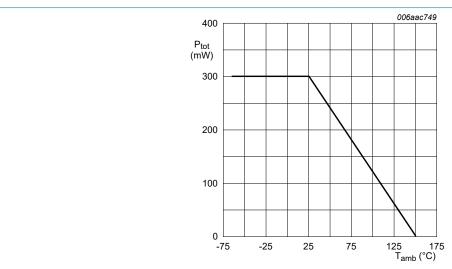
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or		'	•	•	
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
VI	input voltage	positive		-	6	V
		negative		-	-40	V
Io	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	200	mW
Per device	'		'	1	•	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35  $\mu m$  copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

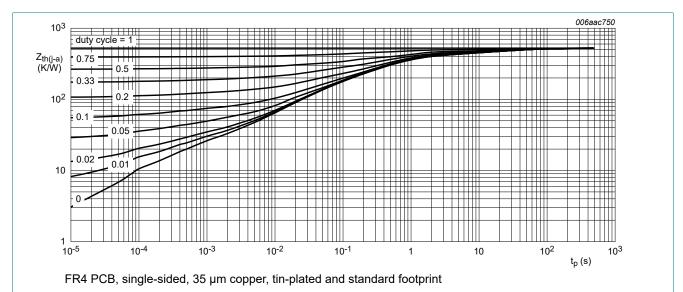


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

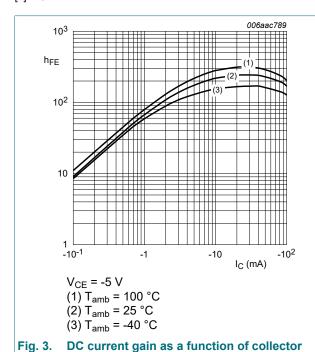
50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

#### 10. Characteristics

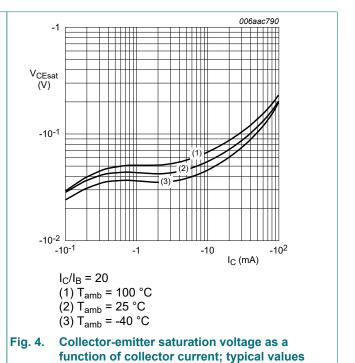
**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	I <sub>C</sub> = -2 mA; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	/ <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-100	nA
	current	V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	-150	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -5 mA; $T_{amb}$ = 25 °C		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	-100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = -5 V; $I_{C}$ = -100 $\mu$ A; $T_{amb}$ = 25 °C		-	-0.7	-0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = -0.3 V; $I_{C}$ = -1 mA; $T_{amb}$ = 25 °C		-1.4	-0.8	-	V
R1	bias resistor 1 (input)			7	10	13	kΩ
R2/R1	bias resistor ratio			3.7	4.7	5.7	
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[1]	-	180	-	MHz

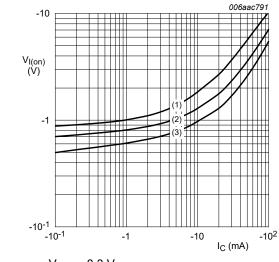
#### [1] Characteristics of built-in transistor



current; typical values

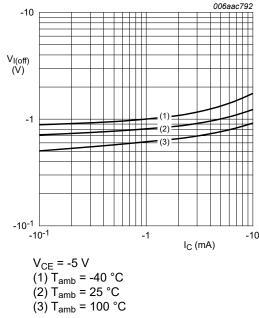


#### 50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$



V<sub>CE</sub> = -0.3 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C





Off-state input voltage as a function of collector current; typical values

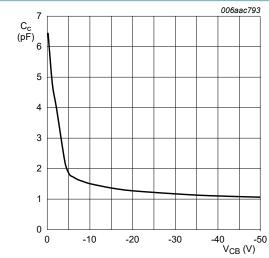


Fig. 7. Collector capacitance as a function of collectorbase voltage; typical values

 $f = 1 MHz; T_{amb} = 25 °C$ 

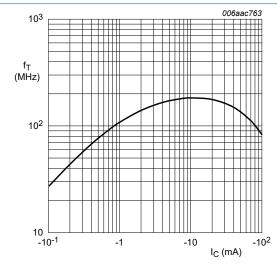


Fig. 8. Transition frequency as a function of collector current; typical values of built-in transistor

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## 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

#### **Resistor calculation**

Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

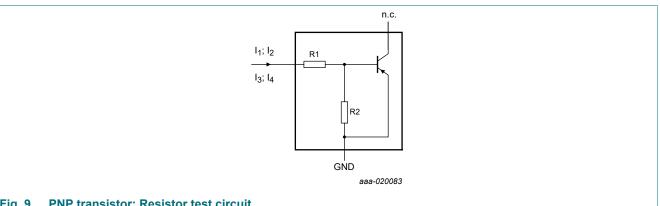


Fig. 9. PNP transistor: Resistor test circuit

#### **Resistor test conditions**

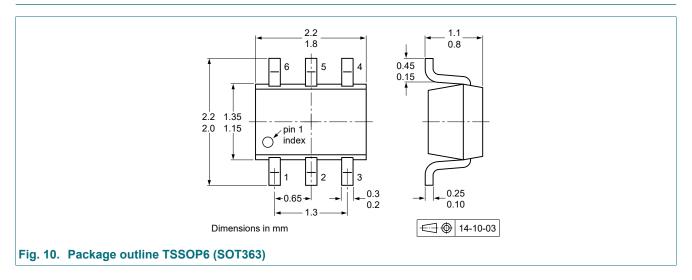
**Table 8. Resistor test conditions** 

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14	
PUMB9	10	47	-140 μA	-90 μΑ	105 μΑ	55 µA	

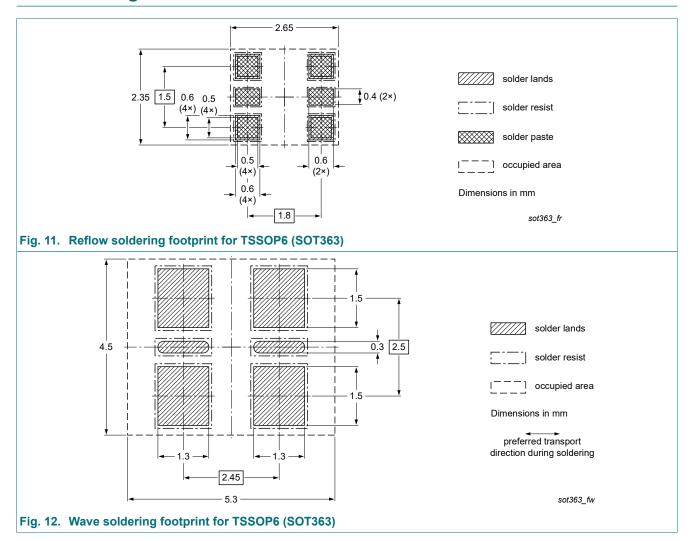
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50 V, 100 mA PNP/PNP resistor-equipped double transistor; R1 = 10 k $\Omega$ , R2 = 47 k $\Omega$ 

## 12. Package outline



## 13. Soldering



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## 14. Revision history

#### Table 9. Revision history

Nexperia.	Product data sheet ta sheet has been redesi en adapted to the new cor	change notice - gned to comply with the i	, 0
The format of this day     Nexperia.	ta sheet has been redesi		identity guidelines of
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	duced to single type data	1 7 11	эрпаю.
20111122	Product data sheet	-	PEMB9_PUMB9 v.2
20031003	Product data sheet	-	PUMB9 v.1 PEMB9 v.1
20030203	Objective specification	-	-
20030107	Product specification	-	-
	<ul><li>Packing information</li><li>20111122</li><li>20031003</li><li>20030203</li></ul>	<ul> <li>Packing information is removed.</li> <li>20111122 Product data sheet</li> <li>20031003 Product data sheet</li> <li>20030203 Objective specification</li> </ul>	20111122 Product data sheet - 20031003 Product data sheet - 20030203 Objective specification -

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## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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